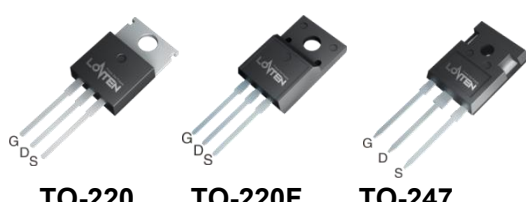
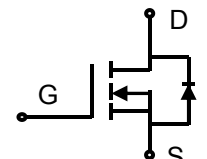


Lonten N-channel 650V, 20A Power MOSFET

Description The Power MOSFET is fabricated using the advanced planer VDMOS technology. The resulting device has low conduction resistance, superior switching performance and high avalanche energy. Features ◆ Low $R_{DS(on)}$ ◆ Low gate charge (typ. $Q_g = 58.3$ nC) ◆ 100% UIS tested ◆ RoHS compliant Applications ◆ Power factor correction. ◆ Switched mode power supplies. ◆ LED driver.	Product Summary <table> <tr> <td>V_{DSS}</td><td>650V</td></tr> <tr> <td>I_D</td><td>20A</td></tr> <tr> <td>$R_{DS(on),max}$</td><td>0.5Ω</td></tr> <tr> <td>$Q_{g,typ}$</td><td>58.3 nC</td></tr> </table>  TO-220 TO-220F TO-247  N-Channel MOSFET	V_{DSS}	650V	I_D	20A	$R_{DS(on),max}$	0.5 Ω	$Q_{g,typ}$	58.3 nC
V_{DSS}	650V								
I_D	20A								
$R_{DS(on),max}$	0.5 Ω								
$Q_{g,typ}$	58.3 nC								

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ($T_C = 25^\circ\text{C}$)	I_D	20	A
($T_C = 100^\circ\text{C}$)		12.5	A
Pulsed drain current ¹⁾	I_{DM}	80	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ²⁾	E_{AS}	720	mJ
Peak diode recovery dv/dt ³⁾	dv/dt	5	V/ns
Power Dissipation TO-220F ($T_C = 25^\circ\text{C}$)	P_D	45	W
Derate above 25°C		0.36	W/ $^\circ\text{C}$
Power Dissipation TO-247/TO-220 ($T_C = 25^\circ\text{C}$)		250	W
Derate above 25°C		2	W/ $^\circ\text{C}$
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Continuous diode forward current	I_S	20	A
Diode pulse current	$I_{S,pulse}$	80	A

Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO-220F	TO-247/TO-220	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	2.78	0.5	$^\circ\text{C/W}$
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	62.5	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device	Device Package	Marking	Units/Tube	Units/Reel
LNB20N65	TO-247	LNB20N65	30	
LND20N65	TO-220F	LND20N65	50	
LNC20N65	TO-220	LNC20N65	50	

Electrical Characteristics T_c = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =0.25 mA	650	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25 mA	2	-	4	V
Drain cut-off current	I _{DSS}	V _{DS} =650 V, V _{GS} =0 V, T _j = 25°C T _j = 125°C	- -	-	1 100	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =10A	-	0.42	0.5	Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	2962	-	pF
Output capacitance	C _{oss}		-	266	-	
Reverse transfer capacitance	C _{rss}		-	18	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 325 V, I _D = 20A R _G = 10 Ω, V _{GS} =15 V	-	18.8	-	ns
Rise time	t _r		-	43.4	-	
Turn-off delay time	t _{d(off)}		-	98.2	-	
Fall time	t _f		-	16.9	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =520 V, I _D =20 A, V _{GS} =0 to 10 V	-	16.7	-	nC
Gate to drain charge	Q _{gd}		-	19.3	-	
Gate charge total	Q _g		-	58.3	-	
Gate plateau voltage	V _{plateau}		-	5	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =20A	-	-	1.5	V
Reverse recovery time	t _{rr}	V _R =325 V, I _F =20A dI _F /dt=100 A/μs	-	492.8	-	ns
Reverse recovery charge	Q _{rr}		-	7.46	-	μC
Peak reverse recovery current	I _{rrm}		-	30.3	-	A

Notes:

1. Pulse width limited by maximum junction temperature.
2. L=10mH, I_{AS} = 12A, Starting T_j= 25°C.
3. I_{SD} = 20A, di/dt≤100A/μs, V_{DD}≤BV_{DS}, Starting T_j= 25°C.

Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

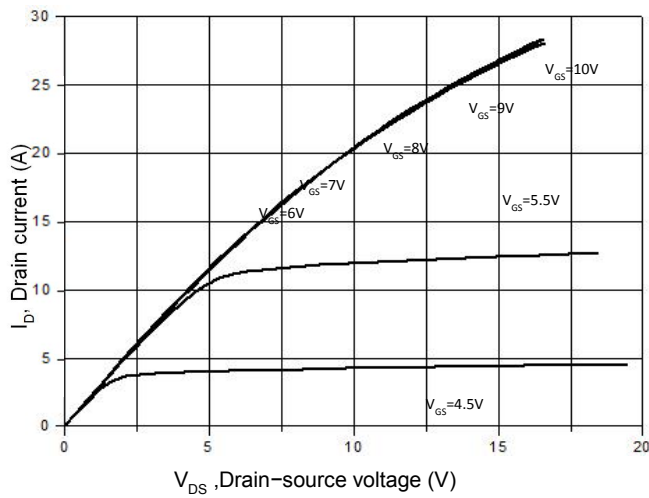


Figure 2. Transfer Characteristics

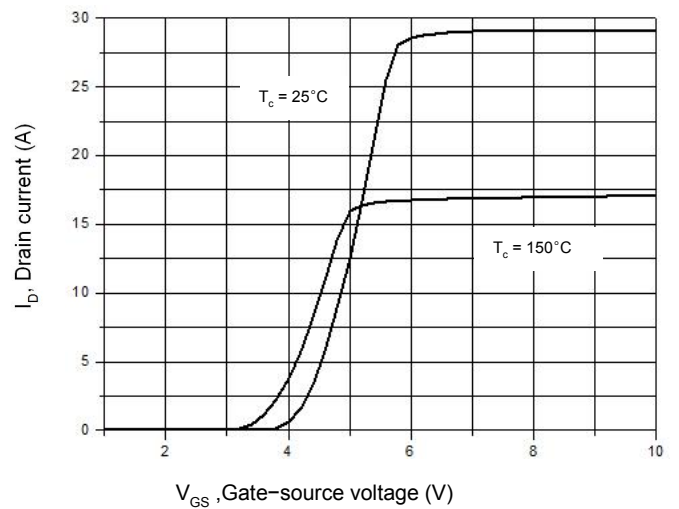


Figure 3. On-Resistance Variation vs. Drain Current

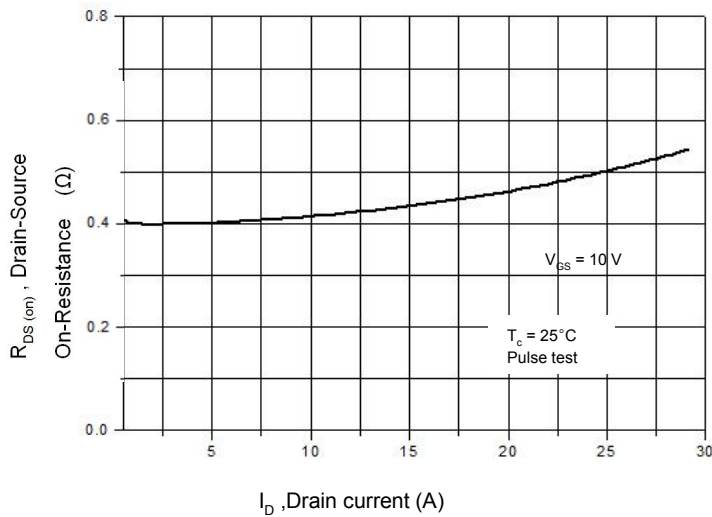


Figure 4. Threshold Voltage vs. Temperature

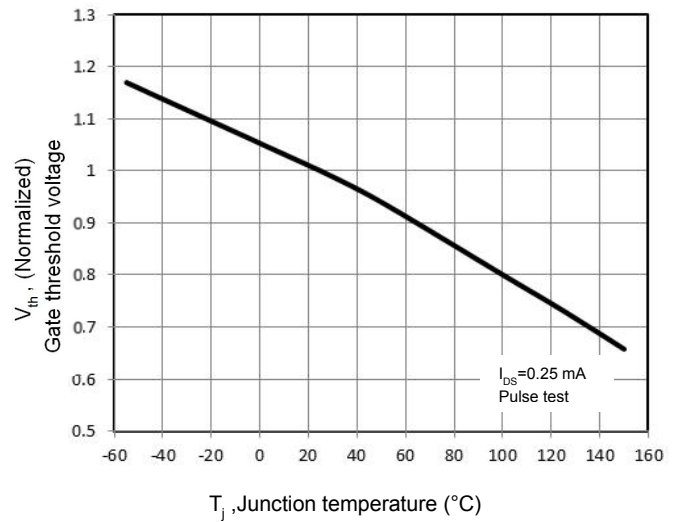


Figure 5. Breakdown Voltage vs. Temperature

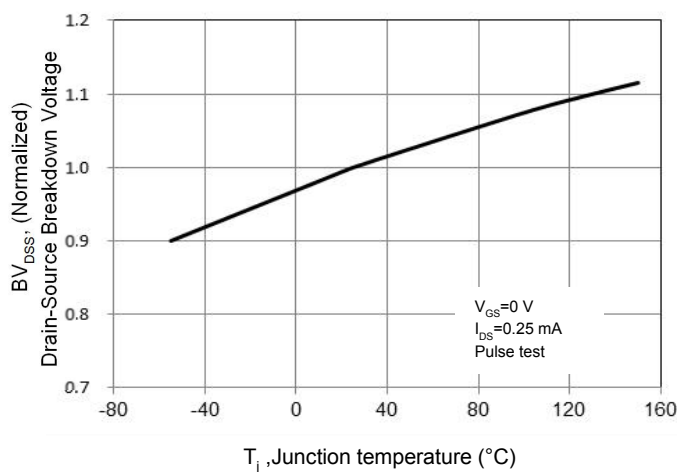


Figure 6. On-Resistance vs. Temperature

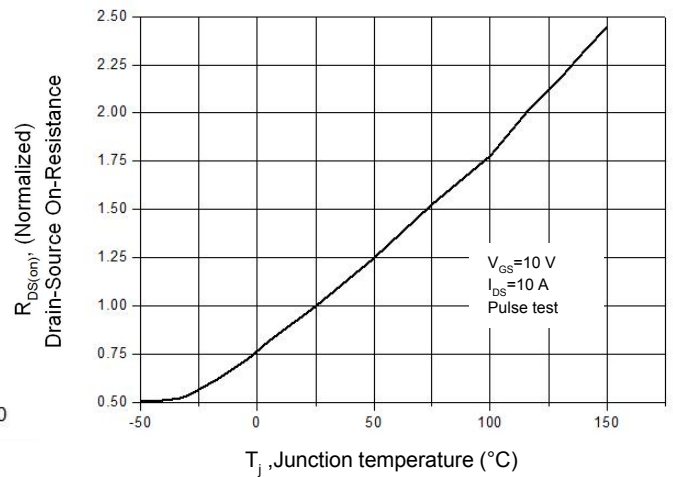


Figure 7. Capacitance Characteristics

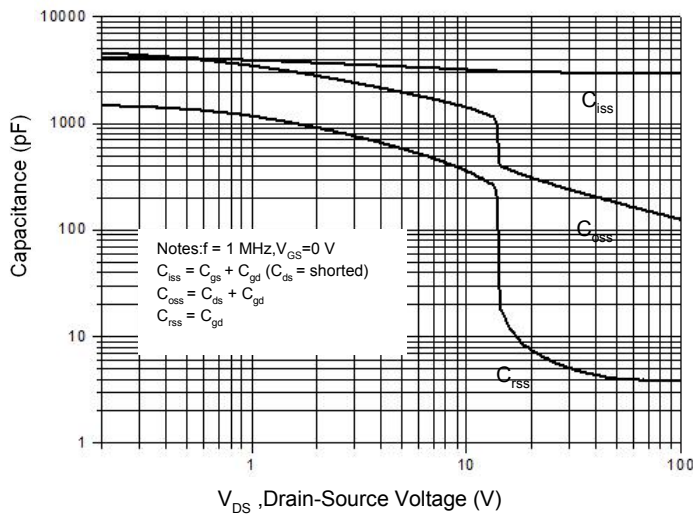


Figure 8. Gate Charge Characteristics

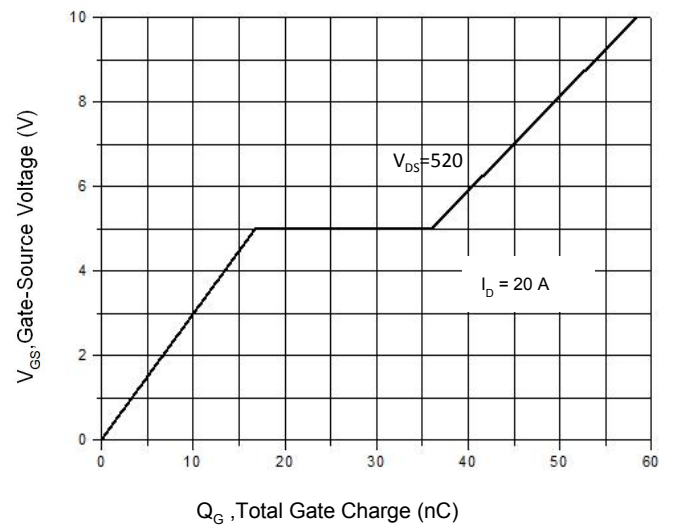


Figure 9. Maximum Safe Operating Area
TO-220F

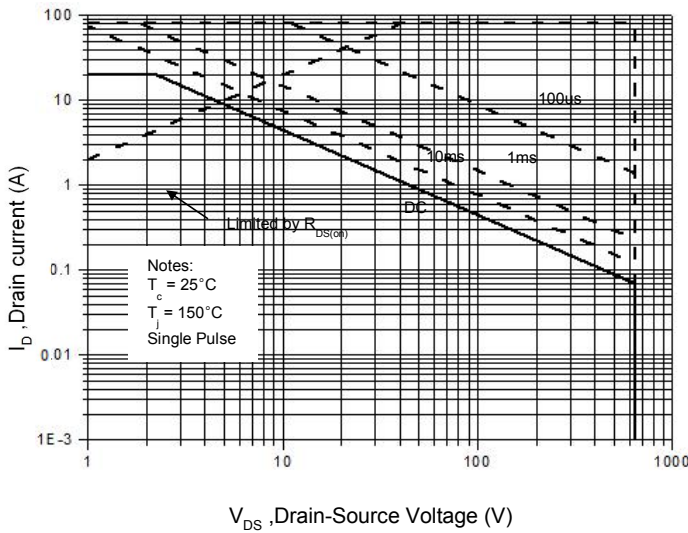


Figure 10. Maximum Safe Operating Area
TO-247/TO-220

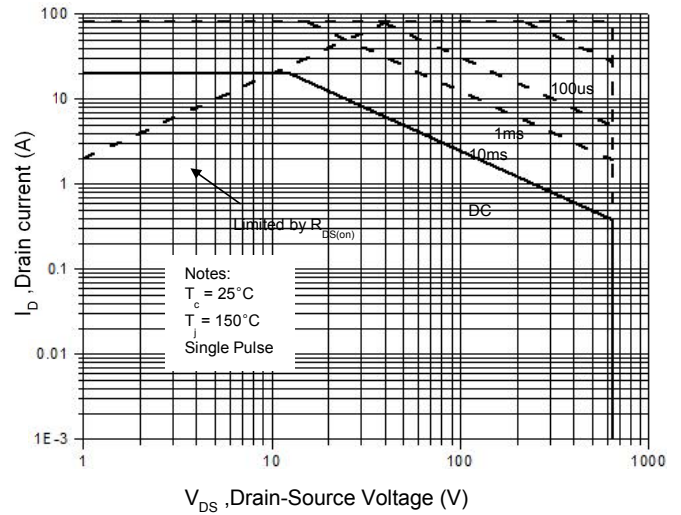


Figure 11. Power Dissipation vs. Temperature
TO-220F

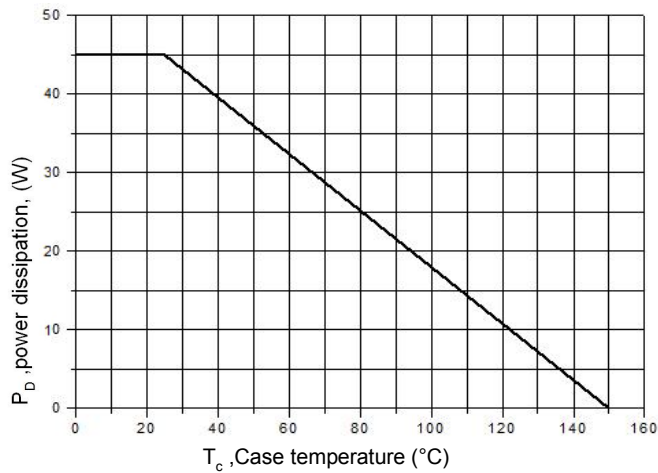


Figure 12. Power Dissipation vs. Temperature
TO-247/TO-220

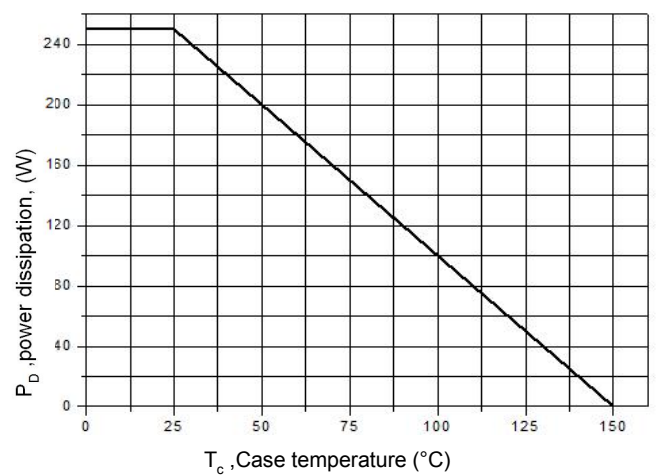


Figure 13. Continuous Drain Current vs. Temperature

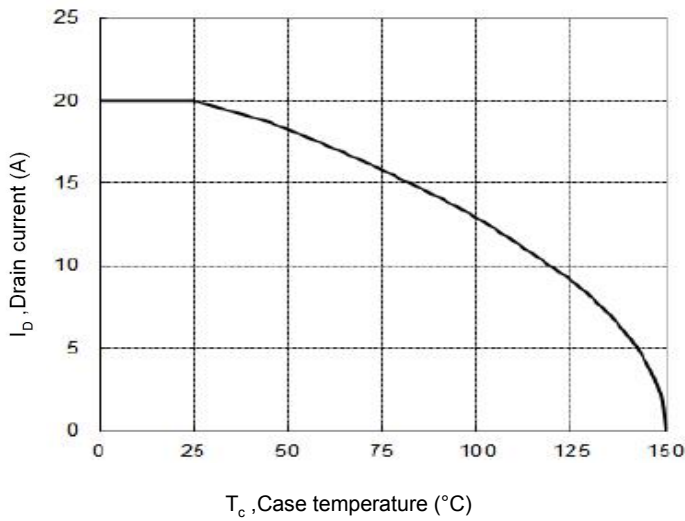


Figure 14. Body Diode Transfer Characteristics

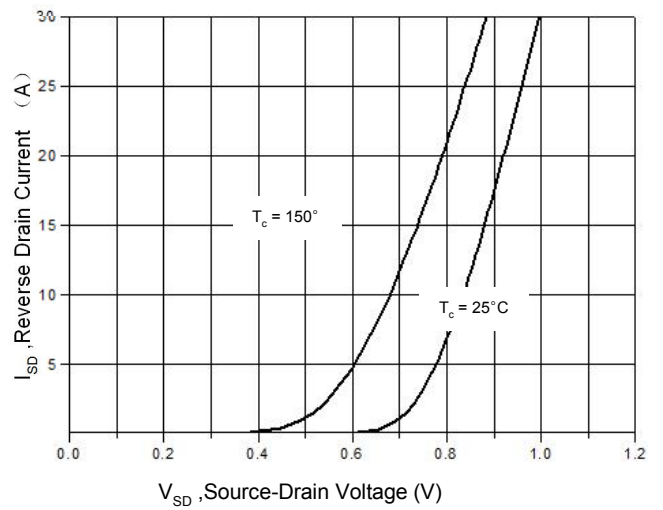


Figure 15 Transient Thermal Impedance , Junction to Case, TO-220F

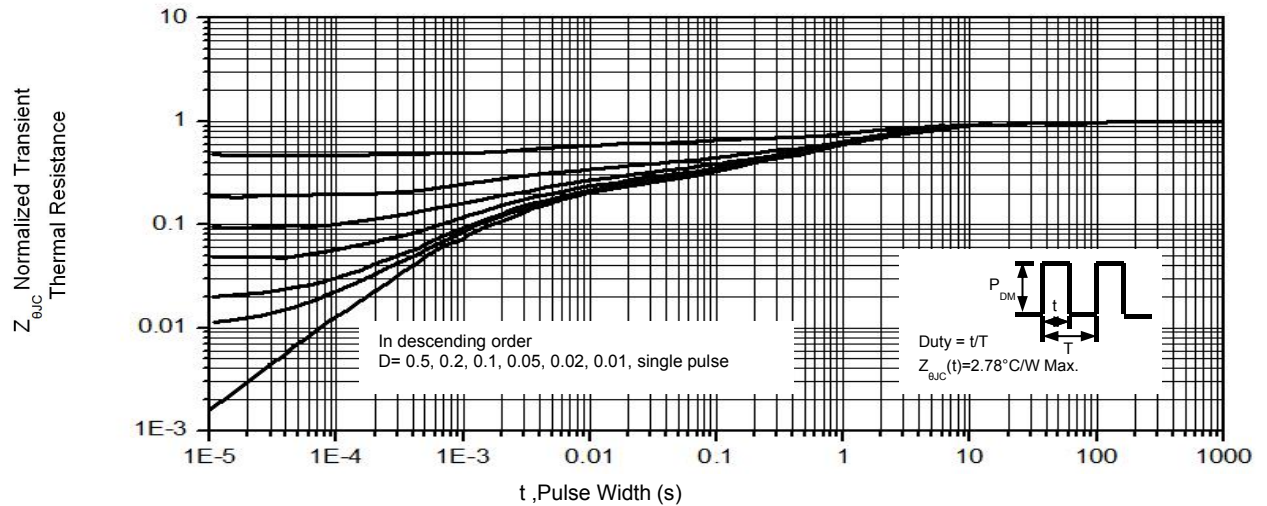
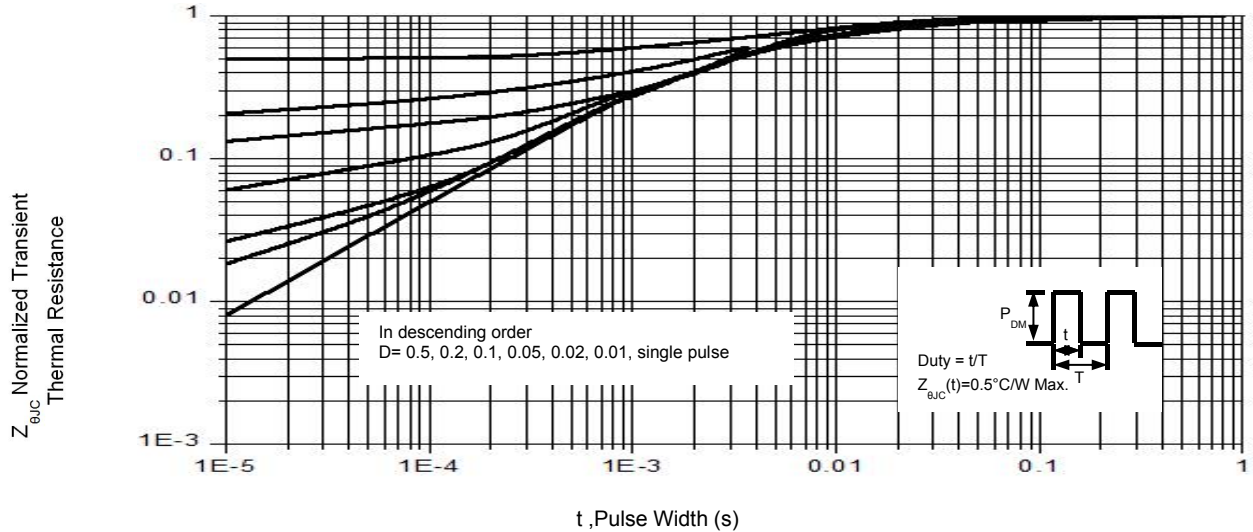
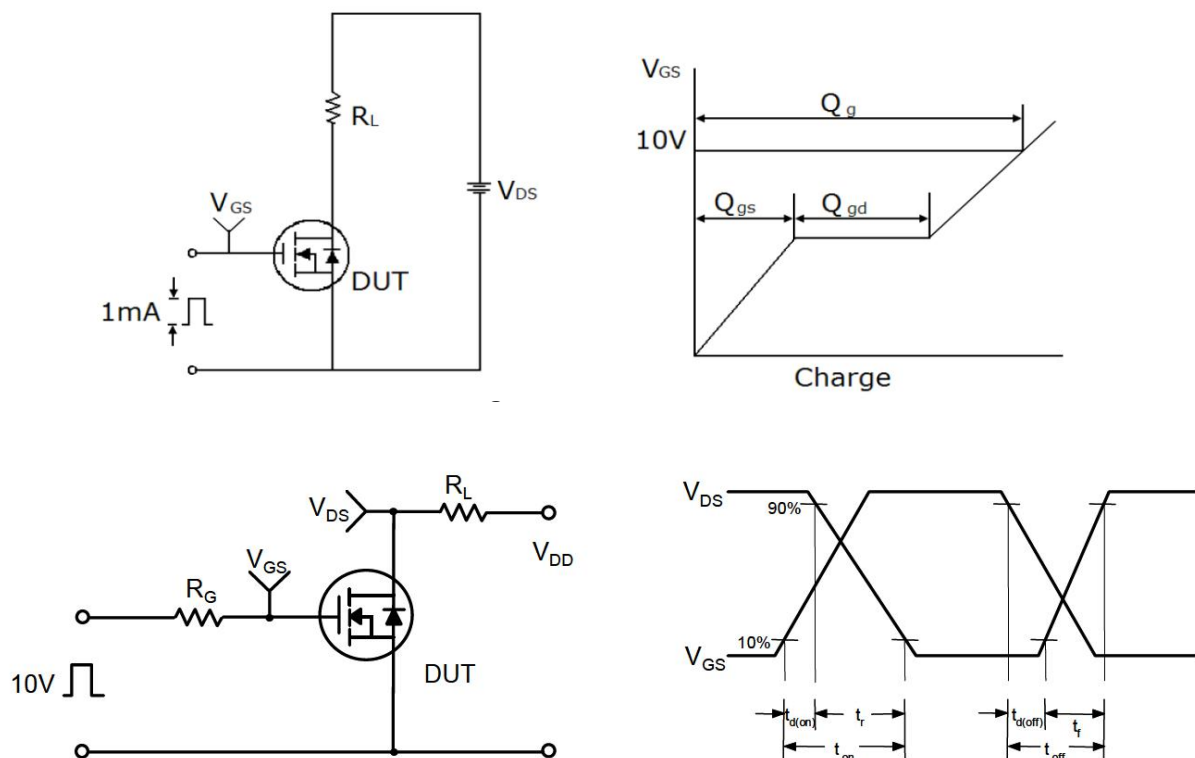


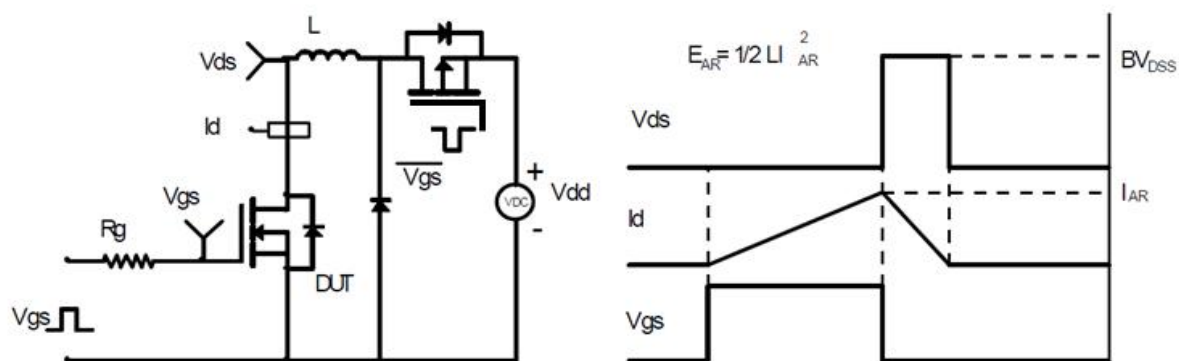
Figure 16. Transient Thermal Impedance, Junction to Case, TO-247/TO-220



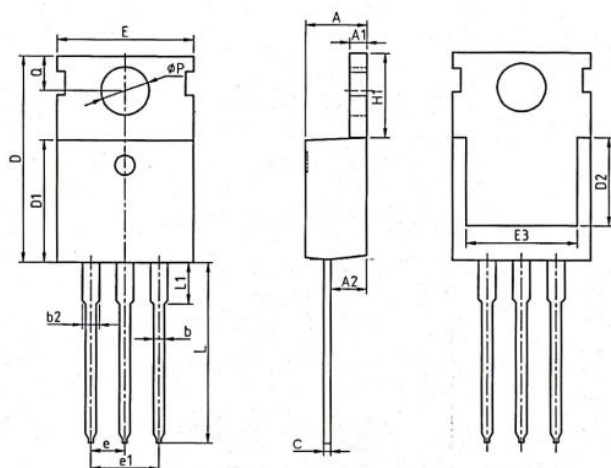
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching Test Circuit & Waveforms

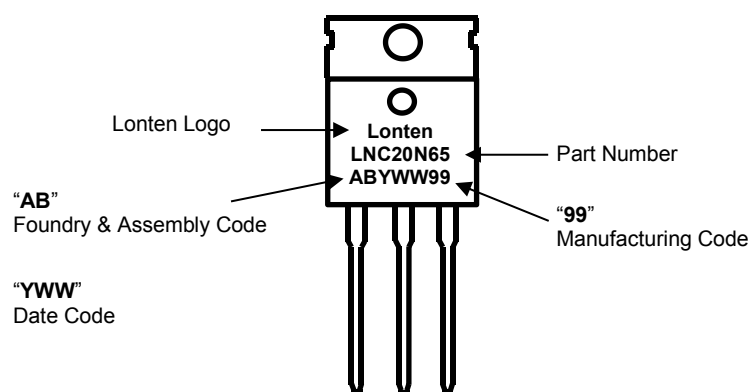


Mechanical Dimensions for TO-220

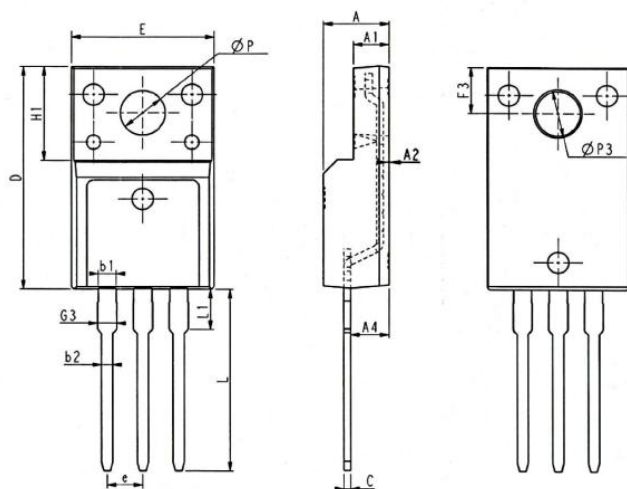


SYMBOL	COMMON DIMENSIONS					
	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.37	4.57	4.70	0.172	0.180	0.185
A1	1.25	1.30	1.40	0.049	0.051	0.055
A2	2.20	2.40	2.60	0.087	0.094	0.102
b	0.70	0.80	0.95	0.028	0.031	0.037
b2	1.17	1.27	1.47	0.046	0.050	0.058
c	0.45	0.50	0.60	0.018	0.020	0.024
D	15.10	15.60	16.10	0.594	0.614	0.634
D1	8.80	9.10	9.40	0.346	0.358	0.370
D2	5.50	—	—	0.217	—	—
E	9.70	10.00	10.30	0.382	0.394	0.406
E3	7.00	—	—	0.276	—	—
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.25	6.50	6.85	0.246	0.256	0.270
L	12.75	13.50	13.80	0.502	0.531	0.543
L1	—	3.10	3.40	—	0.122	0.134
Øp	3.40	3.60	3.80	0.134	0.142	0.150
Q	2.60	2.80	3.00	0.102	0.110	0.118

TO-220 Part Marking Information

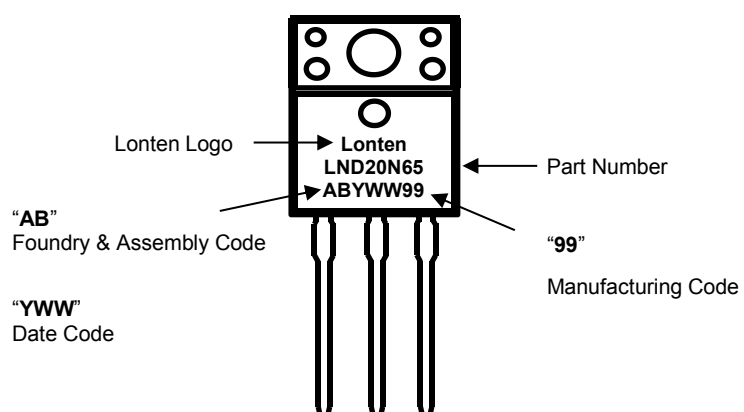


Mechanical Dimensions for TO-220F

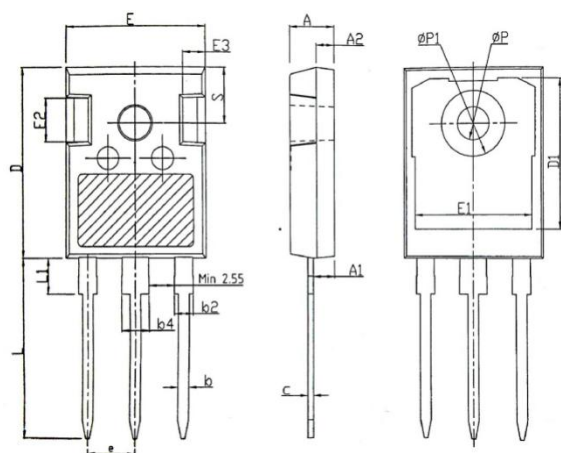


COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408
A	4.50	4.70	4.90	0.177	0.185	0.193
A1	2.34	2.54	2.74	0.092	0.100	0.108
A2	0.30	0.45	0.60	0.012	0.002	0.024
A4	2.65	2.76	2.96	0.104	0.109	0.117
C	0.40	0.50	0.65	0.016	0.020	0.026
D	15.57	15.87	16.17	0.613	0.625	0.637
H1	6.70REF			0.264REF		
e	2.54BSC			0.1BSC		
ØP	3.03	3.18	3.38	0.119	0.125	0.133
L	12.68	12.98	13.28	0.499	0.511	0.523
L1	2.88	3.03	3.18	0.113	0.119	0.125
ØP3	3.15REF			0.124REF		
F3	3.15	3.30	3.45	0.124	0.130	0.136
G3	1.25	1.35	1.55	0.049	0.053	0.061
b1	1.18	1.28	1.43	0.046	0.050	0.056
b2	0.70	0.80	0.95	0.028	0.031	0.037

TO-220F Part Marking Information

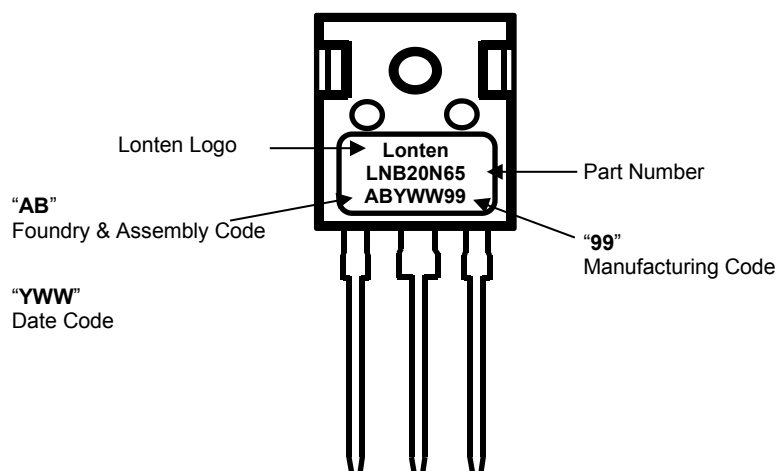


Mechanical Dimensions for TO-247



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.59
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.80	21.00	21.30
D1	16.25	16.55	16.85
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.82	19.92	20.22
L1	—	—	4.30
ØP	3.40	3.60	3.80
ØP1	—	—	7.30
S	6.15BSC		

TO-247 Part Marking Information



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